# Design Guidelines of All Storage Class Memory (SCM) SSD and Hybrid SCM/NAND Flash SSD to Balance Performance, Power, Endurance and Cost

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# Abstract

The performance, energy consumption, endurance and cost are compared between the All storage-type storage class memory (S-SCM) solid-state drive (SSD) and Hybrid memory-type SCM (M-SCM)/NAND flash SSD. A wear leveling algorithm has been proposed for the SCM due to its limited endurance. With a 25% M-SCM/NAND capacity ratio, the All S-SCM SSD is faster if the S-SCM latency is <5µs. Moreover, assuming the cost ratio of M-SCM/NAND is 12, All S-SCM SSD is more cost-efficient when S-SCM/NAND cost ratio is < 4.

# 1. Introduction

Storage class memories (SCMs) are the emerging nonvolatile memories [1, 2]. Since the characteristics of each SCM device are different, memory-type SCM (M-SCM) such as STT-MRAM is named for the DRAM-like SCM with a high performance but low capacity. The NAND flash-like SCM such as ReRAM and PRAM is called storage-type SCM (S-SCM), which has a high capacity while low performance. Fig. 1 describes the switching mechanism of a super-lattice PRAM (SL-PRAM). It can be an ideal candidate for the future high density S-SCM because of the lower SET/RESET current than the GST-PRAM (Fig. 2) [3]. Since the perfect device of high-speed and low-cost does not exist, there is a tradeoff between the speed and cost. For example, the longer word-line and bit-line decrease the chip cost but its larger parasitic resistance and capacitance degrade the performance. For the Hybrid M-SCM/NAND flash solid-state drive (Hybrid SSD), its performance lies between M-SCM and NAND flash. More M-SCM capacity can accelerate the SSD speed but also introduces more cost. Therefore, in this paper, the design guidelines of the All S-SCM SSD and Hybrid SSD are provided considering the performance/cost tradeoff.

# 2. SSD Architecture and Algorithm

The architectures of the All S-SCM SSD and Hybrid SSD [4] are illustrated in Fig. 3. M-SCM is used as a write cache for the NAND flash to merge the frequently accessed data in the Hybrid SSD. S-SCM is adopted for the All S-SCM SSD due to its high capacity. The SSD controller manages the data storage. The algorithm tables are stored in a DRAM. In the Hybrid SSD, hot or fragmented data are buffered in the M-SCM while cold and sequential data are stored in the NAND flash, as shown in Fig. 4(a) [4]. When the M-SCM is almost full, cold and less fragmented data are evicted to the NAND flash. Since the SCM endurance is limited ( $\sim 10^9$ ), wear leveling is required. In the proposed wear leveling algorithm of Fig. 4(b), an overwrite count  $WE_{sector}$  is calculated for each SCM sector (512 Bytes). When the maximum  $WE_{sector}$  of a page surpasses a threshold  $W_{\rm th}$ , the wear leveling procedure is triggered: the old data is read out, merged with the new data and written to a blank SCM page (same page size as the NAND flash), as illustrated in Fig. 5. After that, the old page is recycled as blank and the  $W_{\text{th}}$  of this physical page is updated by adding an overwrite count  $N_{\text{ow}}$ . Fig. 6 demonstrates the developed trace-based simulation platform to evaluate the storage system. The system-level performance, energy consumption and endurance of the memory device are outputted as the evaluation results.

# 3. Results and Discussions

The specifications of the memory devices are listed in Table I. In the Hybrid SSD, the M-SCM capacity is varied from 5% to 25% of the SSD capacity. Workload of the financial server is used for evaluation [5]. Fig. 7 shows the sensitivity analyses of the parameter  $N_{ow}$  for the All S-SCM SSD, whose endurance is the reciprocal of the write/erase (W/E) cycle of the mostly worn sector. As shown in Fig. 7(a), a small  $N_{ow}$  causes degradation of the endurance, because excessively-frequent data migration is harmful to the SCM endurance. Contrarily, a large  $N_{ow}$  leads to an insufficient wear leveling. As a result, write accesses among sectors are not balanced: some sectors are heavily overwritten while others not. From Fig. 7(b), frequent wear leveling procedures degrade the performance of the All SCM SSD. To find the optimum  $N_{ow}$  for balancing performance and endurance, Function(T,E) is defined in Fig. 8, in which T and E are the regularized throughput and endurance. The cross point is considered as a balance point between the throughput and endurance. With this optimal  $N_{ow}$ , the speed of the All SCM SSD and Hybrid SSD are compared in Fig. 9. All S-SCM SSD with a <5 µs access latency is faster than the Hybrid SSD, when the M-SCM/NAND capacity ratio ( $S_{M-SCM/NAND}$ ) is 25%. When  $S_{M-SCM/NAND}$  is <10%, All S-SCM SSD is faster than the Hybrid SSD even S-SCM latency is >10 µs. Assuming the cost of each memory device, the total SSD cost is compared in Fig. 10. The Hybrid SSD with a 25%  $S_{M-SCM/NAND}$  is more cost-effective if the S-SCM/NAND cost ratio ( $R_{\text{S-SCM/NAND}}$ ) is >4.

#### 4. Conclusions

The All S-SCM SSD and Hybrid SSD are compared in the performance, power, endurance and cost. As summarized in Table II, compared with the Hybrid SSD, All S-SCM SSD is faster when the M-SCM/NAND capacity ratio of the Hybrid SSD ( $S_{M-SCM/NAND}$ ) is <10%. When  $S_{M-SCM/NAND}$  is 25%, S-SCM latency has to be <5 µs to make the All S-SCM SSD faster than the Hybrid SSD. The SSD cost comparisons are summarized in Table III, assuming the cost ratio of M-SCM/NAND is 12, if the S-SCM/NAND cost ratio is <4, All S-SCM SSD has lower cost than its hybrid counterpart with a 25%  $S_{M-SCM/NAND}$ .

**References** [1] R.F. Freitas et al., *IBM Journal of Research and Development, vol. 52, no. 4/5*(2008) 439-447. [2] G.W. Burr et al., *IBM Journal of Research and Development, vol. 52, no. 4/5*(2008) 449-464. [3] K. Johguchi at el., IRPS (2013) MY.5.1-MY.5.4 [4] C. Sun *et al., TCAS-I* (2014) 382-392. [5] http://traces.cs.umass.edu/index.php/Storage/Storage



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